

ECELCAB5VU

Ultra-Low Capacitance ESD Protection Diode

The ECELCAB5VU is an uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The ECELCAB5VU has an ultra-low capacitance with a typical value at 0.6pF, and complies with the IEC 61000-4-2 (ESD) with ± 25 kV air and ± 20 kV contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size, ultra-low capacitance and high ESD surge protection make ECELCAB5VU an ideal choice to protect cell phone, digital visual interfaces, HDMI, DVI, USB2.0, USB3.0, and other high speed ports.

Features

- Single-channel ESD protection
- Peak Power Dissipation 80W (8 x 20 us Waveform)
- Protects I/O Port
- Ultralow capacitance 0.6pf
- Low Clamping Voltage
- Low Leakage
- Stand-off Voltage: 5.0V
- RoHS Compliant
- Meets MSL 1 Requirements
- Reliable silicon device avalanche breakdown Structure

Main applications

- USB(2.0/3.0/3.1)
- Cell phone handsets and accessories
- Personal Digital Assistants (PDAs)
- Portable Instrumentation
- Digital Cameras
- MP3/MP4/PMP Players

Protection solution to meet

- IEC61000-4-2 (ESD) ±20 kV (contact), ±25kV (air)
- IEC61000-4-5 (Lightning) 5A (8/20us)

Ordering Information

Device	Package	Qty per Reel	Reel Size
ECELCAB5VU	DFN1006	10000	7 Inch



DFN1006





Maximum ratings (Tamb=25°C Unless Otherwise Specified)				
Parameter	Symbol	Value	Unit	
Peak Pulse Power (tp=8/20µs waveform)	P _{PPP}	80	W	
Peak Pulse Current (8/20µs)	I_{PP}	5	А	
ESD Rating per IEC61000-4-2: Contact	V	20	VV	
Air	V ESD	25	ΚV	
Lead Soldering Temperature	T_L	260 (10 sec.)	°C	
Operating Temperature Range	TJ	-55 ~ 125	°C	
Storage Temperature Range	T _{STG}	-55 ~ 150	°C	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not

normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

*Other voltages may be available upon request.

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			5.0	V	
Breakdown Voltage	V _{BR}	5.6			V	$I_T = 1mA$
Reverse Leakage Current	I _R			0.5	μΑ	$V_{RWM} = 5.0V$
Forward Voltage	$V_{\rm F}$			1.2	V	I _F =10mA
Clamping Voltage	Vc			10	V	$I_{PP} = 1A (8 \times 20 \mu s \text{ pulse})$
Clamping Voltage	Vc			16	V	$I_{PP} = 5A (8 \times 20 \mu s \text{ pulse})$
Junction Capacitance	CJ		0.6	0.8	pF	$V_{R} = 0V, f = 1MHz$

Symbol	Parameter
Vrwm	Working Peak Reverse Voltage
VBR	Breakdown Voltage @ IT
Vc	Clamping Voltage @ IPP
I _T	Test Current
Irm	Leakage current at VRWM
Ірр	Peak pulse current
Co	Off-state Capacitance
CJ	Junction Capacitance



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ECELCAB5VU

Typical electrical characterist applications



Junction Capacitance vs. Reverse Voltage







Clamping Voltage vs. Peak Pulse Current





Power Derating Curve





Package Information

DFN1006

Mechanical Data

Case:DFN1006

Case Material: Molded Plastic. UL Flammability



DIM	Millimeters			
	Min	Max		
Α	0.30	0.50		
A1	0.00	0.05		
D	0.55	0.65		
E	0.95	1.05		
b	0.25	0.60		
e	0.65TYP			
L	0.15	0.35		
L1	0.05REF			

Recommended Pad outline

